ACE3400

N-Channel Enhancement Mode MOSFET

Description

The ACE3400 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

Features

- 30V/5.4A, $R_{DS(ON)}$=38mΩ@V_{GS}=10V
- 30V/4.6A, $R_{DS(ON)}$=42mΩ@V_{GS}=4.5V
- 30V/3.8A, $R_{DS(ON)}$=55mΩ@V_{GS}=2.5V
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

Application

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

Absolute Maximum Ratings

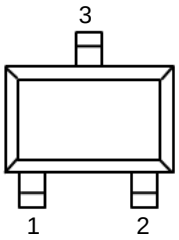
Parameter		Symbol	Max	Unit
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	±12	V
Continuous Drain Current (T_J=150℃)	T_A=25℃	I_D	4.5	A
	T_A=70℃		3.5	
Pulsed Drain Current		I_{DM}	25	A
Continuous Source Current (Diode Conduction)		I_S	1.7	A
Power Dissipation	T_A=25℃	P_D	2.0	W
	T_A=70℃		1.3	
Operating Junction Temperature		T_J	150	°C
Storage Temperature Range		T_{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	90	°C/W

ACE3400

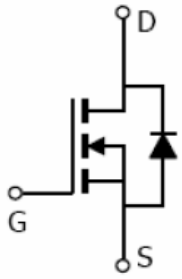
N-Channel Enhancement Mode MOSFET

Packaging Type

SOT-23-3L



SOT-23-3L	Description
1	Gate
2	Source
3	Drain



Ordering information

ACE3400 XX + H

- Halogen - free
- Pb - free
- BM : SOT-23-3L

Electrical Characteristics

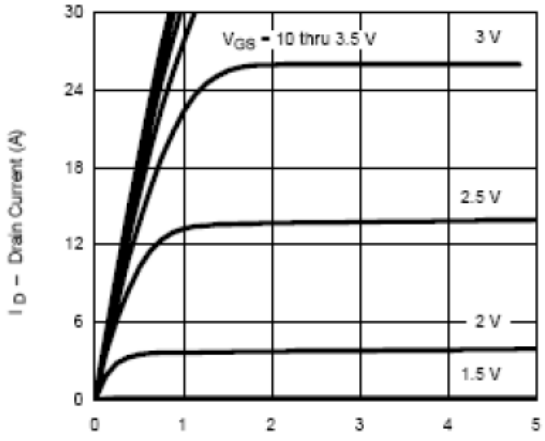
T_A=25℃, unless otherwise noted

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250 uA	30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_D=VGS, I_D=250uA	0.8		1.6	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±12V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=24V, V_{GS}=1.0V			1	uA
		V_{DS}=24V, V_{GS}=0V T_J=55℃			10	
On-State Drain Current	$I_{D(ON)}$	VDS≧4.5V, V_{GS}=4.5V	10			A
Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=5.4A		0.030	0.038	Ω
		V_{GS}=4.5V, I_D=4.6A		0.034	0.042	
		V_{GS}=2.5V, I_D=3.8A		0.040	0.055	
Forward Transconductance	Gfs	V_{DS}=4.5V,I_D=5.4A		12		S
Diode Forward Voltage	V_{SD}	I_S=1.7A, V_{GS}=0V		0.8	1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=15V, V_{GS}=10V, I_D=6.7A		10	18	nC
Gate-Source Charge	Q_{gs}			1.6		
Gate-Drain Charge	Q_{gd}			3.2		
Input Capacitance	Ciss	V_{DS}=15, V_{GS}=0V, f=1MHz		450		pF
Output Capacitance	Coss			240		

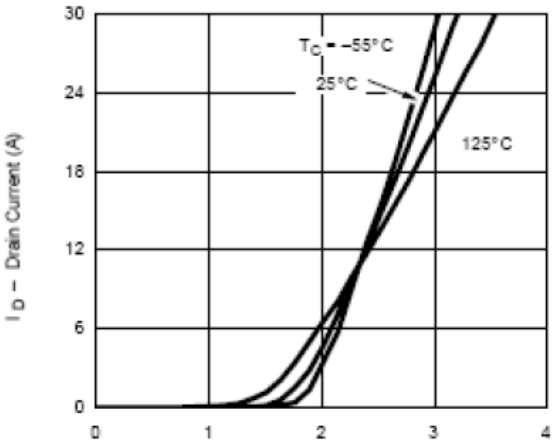
Reverse Transfer Capacitance	Crss			38		
Turn-On Time	td(on)	V_{DD}=15V, R_L=15, I_D=1.0A, V_{GEN}=10V, R_G=6Ω		7	15	nS
	tr			10	20	
Turn-Off Time	td(off)			20	40	
	tf			11	20	

Typical Performance Characteristics

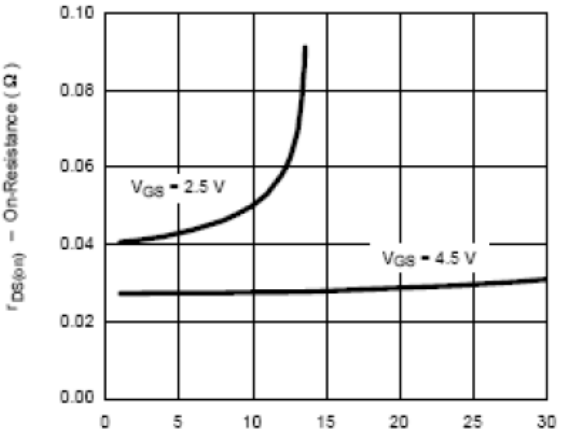
Output Characteristics



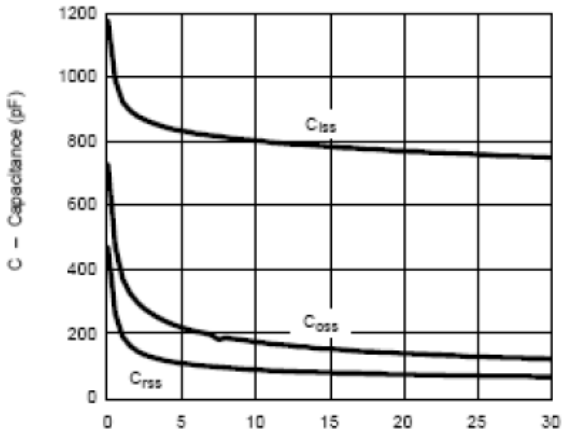
Transfer Characteristics



On-Resistance vs. Drain Current

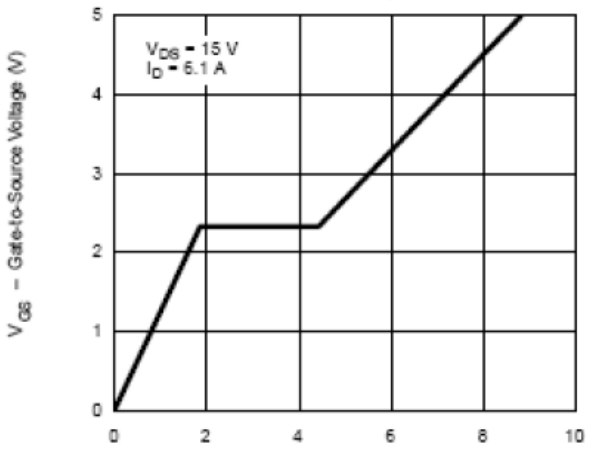


Capacitance



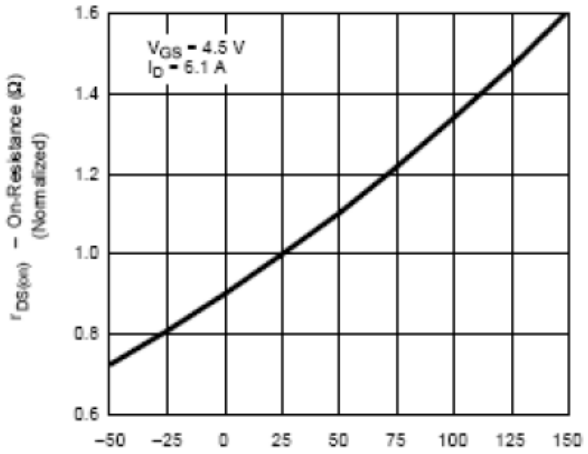
Typical Performance Characteristics

Gate Charge



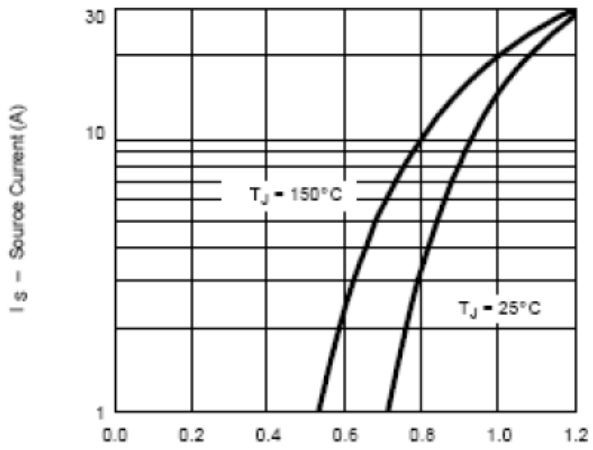
Q_g-Total Gate Charge (nC)

On-Resistance vs. Junction Temperature



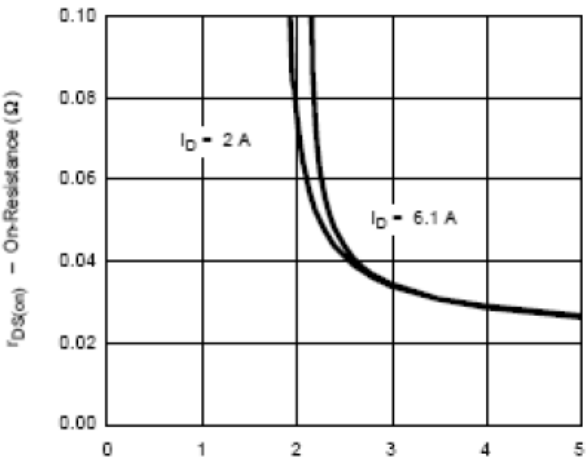
T_J-Junction Temperature (℃)

Source-Drain Diode Forward Voltage



V_{SD}-Source-to-Drain Voltage (V)

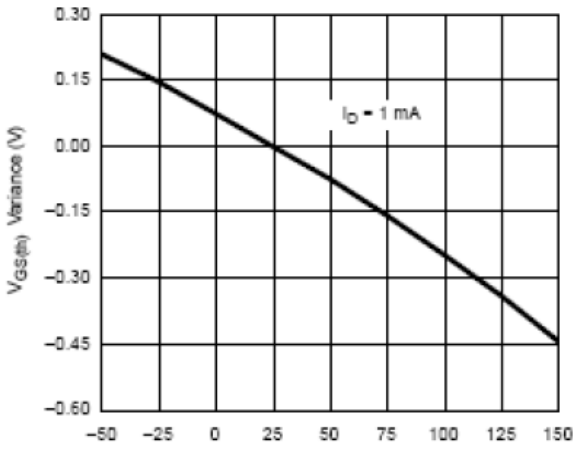
On-Resistance vs. Gate-to-Source Voltage



V_{GS}-Gate-to-Source Voltage (V)

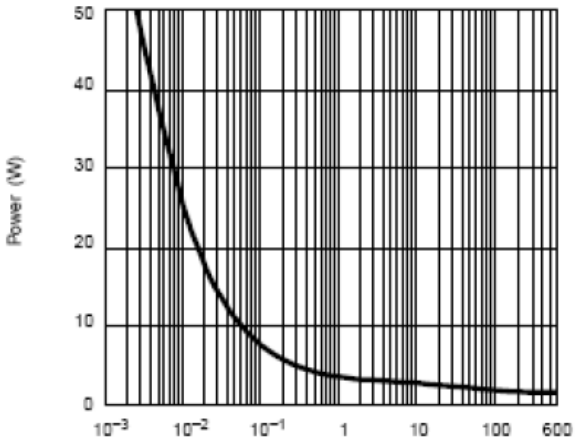
Typical Performance Characteristics

Threshold Voltage



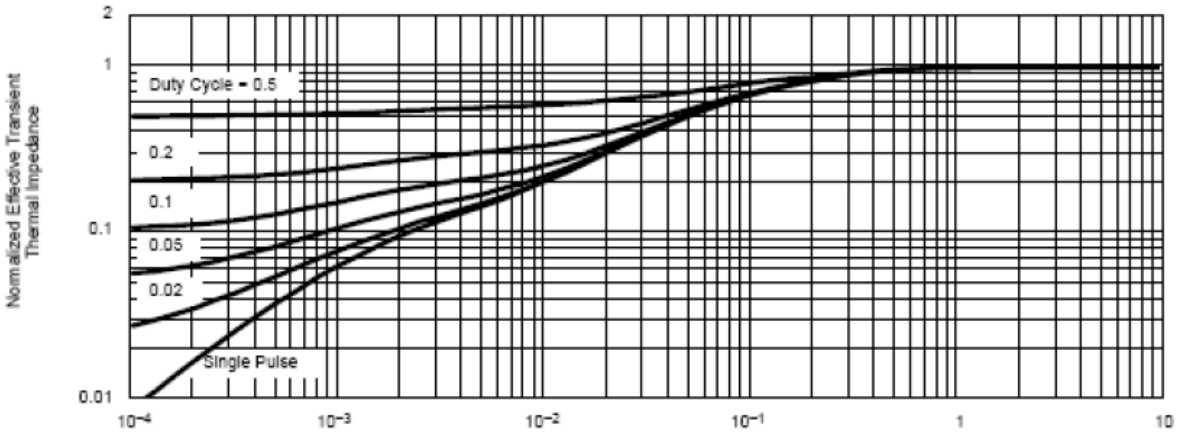
T_J-Temperature(℃)

Single Pulse Power



Time (sec)

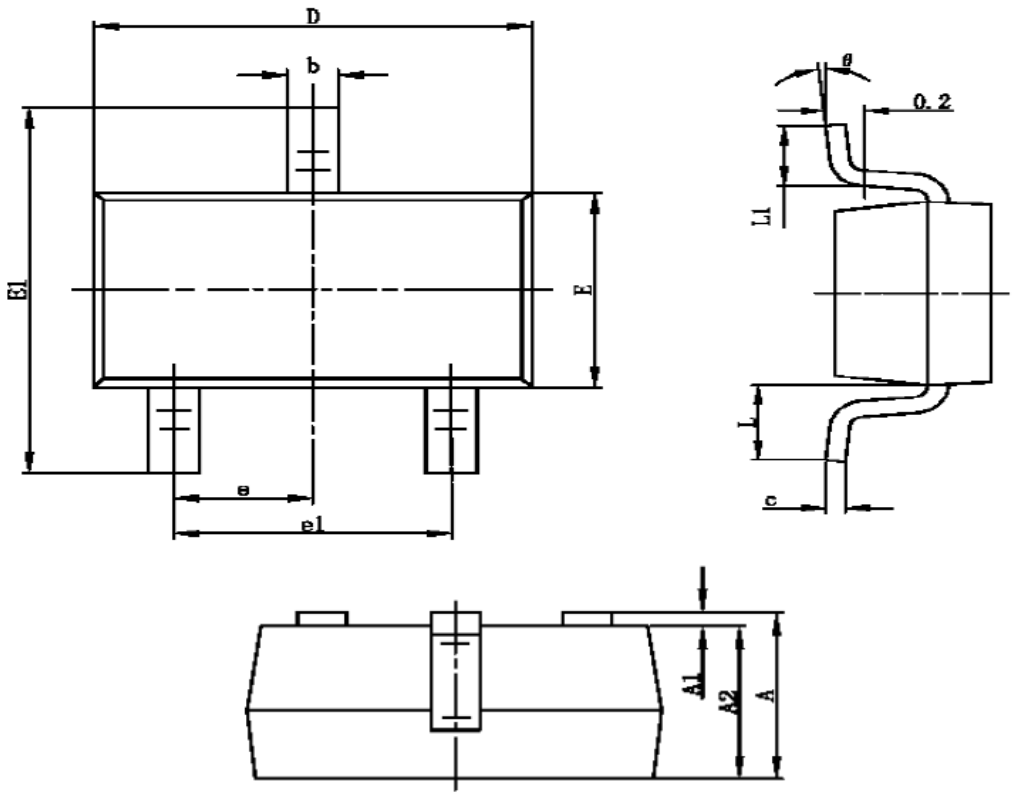
Normalized Thermal Transient Impedance, Junction-to Foot



Square Wave Pulse Duration

Packing Information

SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.400	0.012	0.016
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.700REF		0.028REF	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Notes

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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